

## ABSTRACT

This invention provides a reflective photomask blank and a reflective photomask suppressing or reducing the shadowing effect of a reflective photomask for patterning transfer using a light having a wavelength in the extreme ultraviolet region as a light source and having high interlayer adhesion between a capping layer and a low reflective part. A reflective photomask blank (10) according to this embodiment includes a substrate (1), a reflective part (5), and a low reflective part (4), in which the reflective part (5) includes a multi-layer reflective film (2) and a capping layer (3), the capping layer (3) contains Ru, the low reflective part (4) contains 40 at% or more of a material selected from Ag, Co, In, Pt, Sn, Ni, and Te, and compounds thereof, and a region at least 2 nm thick from the capping layer (3) side of the low reflective part (4) contains 25 at % or more of a material belonging to a first material group or 30 at% or more of a material belonging to a second material group, and the total film thickness of the low reflective part (4) is 45 nm or less.

FIG. 1